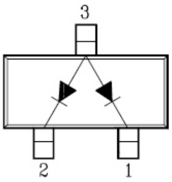
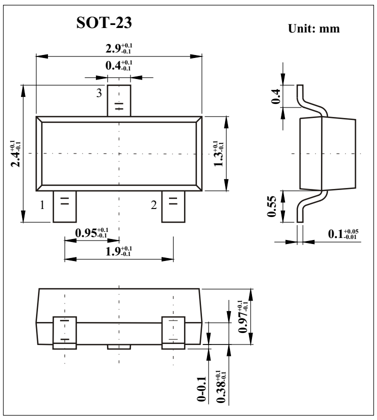
Silicon Epitaxial Planar Diode
KDS181-RTR

■ Features

- ● Low forward voltage : $V_{F(3)}$ = 0.92 V(Typ)
- ● Fast reverse recovery time : t_{rr} = 1.6ns (MAX.)
- ● Small total capacitance : C_T = 2.2pF(Typ)





■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	85	V
Reverse voltage	V_R	80	V
Average forward current	I_O	100	mA
Maximum (peak) forward current	I_{FM}	300	mA
Surge current (10 ms)	I_{FSM}	2	A
Power dissipation	P_D	150	mW
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	$V_{F(1)}$	I_F = 1 mA		0.61		V
	$V_{F(2)}$	I_F = 10 mA		0.74		
	$V_{F(3)}$	I_F = 100 mA		0.92	1.20	
Reverse current	I_R	V_R = 80 V			0.5	μA
Total capacitance	C_T	V_R = 0, f = 1.0 MHz		2.2	4.0	pF
Reverse recovery time	t_{rr}	I_F = 10 mA		1.6	4.0	ns

■ Marking

Marking	A3

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■ Typical Characteristics